PRODUCT DATA

Micro International, Inc

PART NUMBER

LDT918 and LDT918T

Micro-LID NPN Transistor

Micro International, Inc.
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Micro-LID Transistors
LDT918 and LDT918T

Description:

The LDT918 (untinned) and LDT918T (tinned) are NPN silicon transistors in very small, rugged, surface mount, 4-post ceramic packages (Micro International manufactured package p/n 4-075-1). The LDT918 and LDT918T meet the general specifications of the 2N918 transistor. The 4-075-1 Micro-LID package is a 4-post, leadless ceramic carrier which can be provided with gold metallized or pre-tinned lands, and is approved for military, medical implant, sensor, and high reliability applications. The LDT918 and LDT918T can be provided with special feature options such as additional temperature cycling and screening.

Maximum Ratings:

Parameter	Symbol	Rating
Collector-Base Voltage	Vcbo	30 V
Collector-Emitter Voltage	Vceo	15 V
Emitter-Base Voltage	Vebo	3 V
Collector Current	Ic	50 mA
Total Dissipation	Pt	400 mW
Operating Junction Temperature	Tj	150°C
Storage Temperature	Tstg	-65°C to 150°C
Operating Temperature	Toper	-55°C to 125°C

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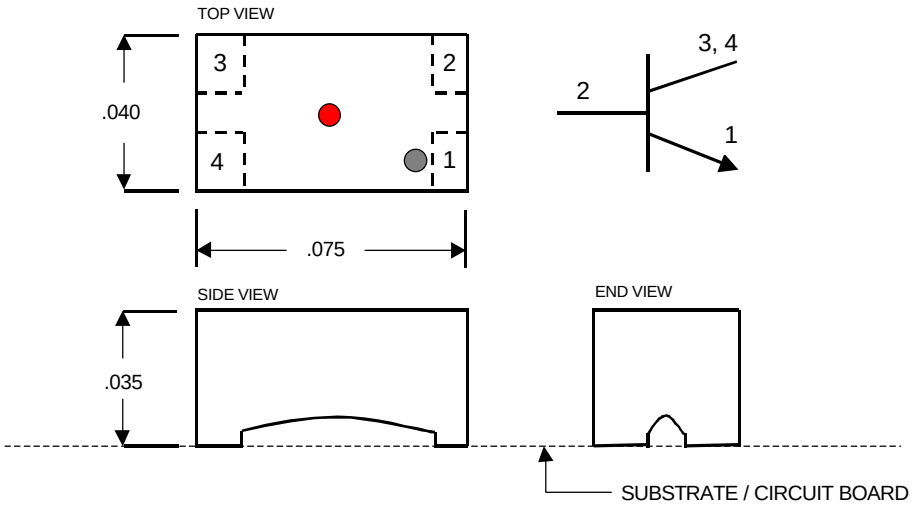
Outline / Schematic:



Dimensions / Marking:

Length	.075″ ± .003″	Post 1 (Emitter)	.015″ x .010″ typ
Width	.040″ ± .003″	Post 2 (Base)	.015″ x .010″ typ
Height	.035″ ± .003″	Post 3,4 (Collector)	.015″ x .012″ typ

Marking on back of package : Gray Dot over Emitter and Red Dot in Center
(post down configuration)

Standard In-Process Screening Requirements:

- Semiconductor die and Micro-LID package visual inspection
- Wire pull test
- 24 hour stabilization bake at 150°C
- 10 temperature cycles from –55°C to 125°C
- 100% electrical test of dc characteristics at 25°C
- Final visual inspection

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Electrical Characteristics (25°C Ambient)

Parameter	Symbol	Min	Typ	Max	Units
Collector-Base Breakdown Ic = 10 uA, Ie = 0	BVcbo	30	--	--	V
Collector-Emitter Breakdown* Ib = 0, Ic = 10 mA	BVceo	15	--	--	V
Emitter-Base Breakdown Ic = 0, Ie = 10 uA	BVebo	3	--	--	V
Collector-Base Cutoff Current Vcb = 15 V	Icbo	--	--	10	nA
DC Forward Current Gain* Ic = 3 mA, Vce = 1 V Ic = 10 mA, Vce = 10 V	Hfe	 20 20	 -- --	 200 --	
Collector-Emitter Saturation Ic = 10 mA, Ib = 1 mA	Vce (sat)	--	--	.4	V
Base-Emitter Saturation Ic = 10 mA, Ib = 1 mA	Vbe (sat)	--	--	1	V
Collector Capacitance Vcb = 10 V, Ie = 0 f = 1 MHz	Cobo	--	--	1.7	pF

* Pulse test, pulse width $\leq$ 300 usec, duty cycle $\leq$ 2%